

DESCRIPTION

METHODS OF FORMING PLURALITIES OF CAPACITORS

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TECHNICAL FIELD

This invention relates to methods of forming pluralities of capacitors.

BACKGROUND ART

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Capacitors are one type of component which is commonly used in the fabrication of integrated circuits, for example in DRAM circuitry. A typical capacitor is comprised of two conductive electrodes separated by a non-conducting dielectric region. As integrated circuitry density has increased, there is a continuing challenge to maintain sufficiently high storage capacitance despite typical decreasing capacitor area. The increase in density of integrated circuitry has typically resulted in greater reduction in the horizontal dimension of capacitors as compared the vertical dimension. In many instances, the vertical dimension of capacitors has increased.

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One manner of forming capacitors is to initially form an insulative material within which a capacitor storage node electrode is formed. For example, an array of capacitor electrode openings for individual capacitors is typically fabricated in such insulative capacitor electrode-forming material, with a typical insulative electrode-forming material being silicon dioxide doped with one or both of phosphorus and boron. The capacitor electrode openings are typically formed by etching. However, it can be difficult to etch the capacitor electrode openings within the insulative material, particularly where the openings are deep.

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Further and regardless, it is often desirable to etch away most if not all of the capacitor electrode-forming material after individual capacitor electrodes have been formed within the openings. Such enables outer sidewall surfaces of the electrodes to provide increased area, and thereby increased capacitance for the capacitors being formed. However, the capacitor electrodes formed in deep openings are typically correspondingly much taller than they are wide. This can lead to toppling of the capacitor electrodes either during the etch to expose the outer sidewall surfaces,

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during transport of the substrate, and/or during deposition of the capacitor dielectric layer or outer capacitor electrode layer. Our U.S. Patent No. 6,667,502 teaches provision of a brace or retaining structure intended to alleviate such toppling.

5 While the invention was motivated in addressing the above identified issues, it is in no way so limited. The invention is only limited by the accompanying claims as literally worded, without interpretative or other limiting reference to the specification, and in accordance with the doctrine of equivalents.

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SUMMARY

The invention includes methods of forming pluralities of capacitors. In one implementation, a method of forming a plurality of capacitors includes providing a plurality of capacitor electrodes within a capacitor array area
15 over a substrate. The capacitor electrodes comprise outer lateral sidewalls. The plurality of capacitor electrodes is supported at least in part with a retaining structure which engages the outer lateral sidewalls. The retaining structure is formed at least in part by etching a layer of material which is not masked anywhere within the capacitor array area to form said retaining
20 structure. The plurality of capacitor electrodes is incorporated into a plurality of capacitors.

In one implementation, a method of forming a plurality of capacitors includes forming different composition first, second and third materials over a capacitor electrode-forming material. The first, second and third materials
25 are received at least in part at some common elevation over the capacitor electrode-forming material. The second material comprises an anisotropically etched retaining structure. The first material is etched substantially selectively relative to the second and third materials followed by etching the capacitor electrode-forming material substantially selectively
30 relative to the second and third materials effective to form a plurality of capacitor electrode openings. Individual capacitor electrodes are formed within individual of the capacitor electrode openings. The third material is etched substantially selectively relative to the second material and substantially selectively relative to the capacitor electrodes effective to
35 expose capacitor electrode-forming material underlying said third material

being etched. This is followed by etching the capacitor electrode-forming material substantially selectively relative to the second material and substantially selectively relative to the capacitor electrodes effective to expose outer lateral sidewalls of the capacitor electrodes and leave at least some of the retaining structure supporting the capacitor electrodes. The plurality of capacitor electrodes is incorporated into a plurality of capacitors.

Other aspects and implementations are contemplated.

BRIEF DESCRIPTION OF THE DRAWINGS

10 Preferred embodiments of the invention are described below with reference to the following accompanying drawings.

Preferred embodiments of the invention are described below with reference to the following accompanying drawings.

15 Fig. 1 is a fragmentary diagrammatic section of a semiconductor wafer fragment in process in accordance with an aspect of the invention.

Fig. 2 is an alternate embodiment to that depicted by Fig. 1.

Fig. 3 is a top view of the left portion of Fig. 1 at a processing step subsequent to that of Fig. 1.

20 Fig. 4 is a view of the Fig. 3, with the left portion of Fig. 4 being taken through line 4-4 in Fig. 3.

Fig. 5 is a view of the Fig. 3 substrate, with the left portion of Fig. 5 being taken through line 5-5 in Fig. 3.

Fig. 6 is a view of the Fig. 4 substrate at a processing step subsequent to that shown by Fig. 4.

25 Fig. 7 is a view of the Fig. 5 substrate at a processing step subsequent to that shown by Fig. 5 and corresponding in sequence to that of Fig. 6.

Fig. 8 is a top view of the Fig. 3 substrate at a processing step subsequent to that of Fig. 3 and subsequent to that of Figs. 6 and 7.

30 Fig. 9 is a view of the Fig. 7 substrate at a processing step subsequent to that shown by Fig. 7 and corresponding in sequence to that of Fig. 8, with the left portion of Fig. 9 being taken through line 9-9 in Fig. 8.

Fig. 10 is a view of the Fig. 6 substrate at a processing step subsequent to that shown by Fig. 6 and corresponding in sequence to that of

Fig. 8, with the left portion of Fig. 10 being taken through line 10-10 in Fig. 8.

Fig. 11 is a top view of the Fig. 8 substrate at a processing step subsequent to that of Fig. 8.

5 Fig. 12 is a view of the Fig. 9 substrate at a processing step subsequent to that shown by Fig. 9 and corresponding in sequence to that of Fig. 11, with the left portion of Fig. 12 being taken through line 12-12 in Fig. 11.

10 Fig. 13 is a view of the Fig. 10 substrate at a processing step subsequent to that shown by Fig. 10 and corresponding in sequence to that of Fig. 11, with the left portion of Fig. 13 being taken through line 13-13 in Fig. 11.

Fig. 14 is a view of the Fig. 13 substrate at a processing step subsequent to that shown by Fig. 13.

15 Fig. 15 is a view of the Fig. 12 substrate at a processing step subsequent to that shown by Fig. 12 and corresponding in sequence to that of Fig. 14.

Fig. 16 is a top view of the Fig. 11 substrate at a processing step subsequent to that of Fig. 11 and subsequent to that of Figs. 14 and 15.

20 Fig. 17 is a view of the Fig. 14 substrate at a processing step subsequent to that shown by Fig. 14 and corresponding in sequence to that of Fig. 16, with the left portion of Fig. 17 being taken through line 17-17 in Fig. 16.

25 Fig. 18 is a view of the Fig. 15 substrate at a processing step subsequent to that shown by Fig. 15 and corresponding in sequence to that of Fig. 16, with the left portion of Fig. 18 being taken through line 18-18 in Fig. 16.

Fig. 19 is a top view of the Fig. 16 substrate at a processing step subsequent to that of Fig. 16.

30 Fig. 20 is a view of the Fig. 18 substrate at a processing step subsequent to that shown by Fig. 18 and corresponding in sequence to that of Fig. 19, with the left portion of Fig. 20 being taken through line 20-20 in Fig. 19.

Fig. 21 is a view of the Fig. 17 substrate at a processing step subsequent to that shown by Fig. 17 and subsequent to that shown by Figs. 19 and 20.

Fig. 22 is a view of the Fig. 20 substrate at a processing step subsequent to that shown by Fig. 20 and corresponding in sequence to that of Fig. 21.

Fig. 23 is a view of the left portion of the Fig. 21 substrate at a processing step subsequent to that shown by Fig. 21.

Fig. 24 is a view of the left portion of the Fig. 22 substrate at a processing step subsequent to that shown by Fig. 22 and corresponding in sequence to that of Fig. 23.

Fig. 25 is a top view of an alternate embodiment.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

This disclosure of the invention is submitted in furtherance of the constitutional purposes of the U.S. Patent Laws "to promote the progress of science and useful arts" (Article 1, Section 8).

Referring to Fig. 1, a semiconductor substrate in process in accordance with an aspect of the invention is indicated generally with reference to numeral 10. Such comprises a substrate which in one exemplary embodiment comprises a semiconductor substrate, for example comprised of bulk monocrystalline silicon or other material. In the context of this document, the term "semiconductor substrate" or "semiconductive substrate" is defined to mean any construction comprising semiconductive material, including, but not limited to, bulk semiconductive materials such as a semiconductive wafer (either alone or in assemblies comprising other materials thereon), and semiconductive material layers (either alone or in assemblies comprising other materials). The term "substrate" refers to any supporting structure, including, but not limited to, the semiconductive substrates described above. Further in the context of this document, the term "layer" encompasses both the singular and the plural, unless otherwise indicated.

The discussion proceeds in a preferred embodiment method of forming an array of capacitors, for example as might be utilized in DRAM or other memory circuitry constructions. Substrate fragment 10 can be

considered as comprising a region 14 and a region 16. In but one implementation, region 14 in one preferred embodiment comprises a capacitor array area and region 16 comprises a circuitry area peripheral to capacitor array area 14. Further by way of example only, substrate
5 fragment 10 is depicted as comprising an insulative layer 18 having a plurality of conductive contact plugs 19 and 21 formed therein for electrical connection with respect to capacitor electrodes of a plurality of capacitors, as will be apparent from the continuing discussion. Insulative material 18 would overlie other substrate material (not shown), for example bulk
10 monocrystalline silicon, semiconductor-on-insulator circuitry or other substrate material whether existing or yet-to-be developed. Exemplary preferred insulative material 18 includes silicon dioxide doped with at least one of boron and phosphorus, for example borophosphosilicate glass (BPSG). Conductive plugs 19 and 21 will comprise one or more conductive
15 materials, perhaps including for example conductively doped semiconductive material. Substrate 18/19/21 is exemplary only, and any conceivable substrate is contemplated whether existing or yet-to-be developed.

A first material 20 has been formed over substrate 18/19/21. An exemplary preferred material is BPSG, with an exemplary preferred
20 thickness range being from 1,000 Angstroms to 20,000 Angstroms. Capacitor electrodes will be formed within material 20 as will be apparent from the continuing discussion, and accordingly material 20 might be considered as capacitor electrode-forming material. First material 20 might be electrically insulative, electrically conductive, or semiconductive, with
25 electrically insulative being most preferred. Capacitor electrode-forming material 20 might comprise a single, homogenous layer as depicted in Fig. 1, might be non-homogenous (for example two or more layers of BPSG with different dopant levels), and further by way of example only might comprise a plurality of discrete layers. For example and by way of example
30 only, Fig. 2 depicts an alternate embodiment substrate fragment 10a. Like numerals from the first described embodiment have been utilized where appropriate, with differences being indicated with the suffix "a" or with different numerals. Fig. 2 depicts capacitor electrode-forming material/first material 20a as comprising at least two layers 22 and 24. By way of

example only, layer 22 might comprise an etch stop layer (i.e. silicon nitride, aluminum oxide, etc.) with layer 24 comprising BPSG.

Referring to Figs. 3-5, a plurality of spaced masking blocks 25, 26, 27, 28, 29, 30, 31, 32 and 33 have been formed over first material 20. Such
5 define respective capacitor electrode opening outlines 25b, 26b, 27b, 28b, 29b, 30b, 31b, 32b, and 33b. By way of example only, a preferred manner of forming the depicted masking blocks with their corresponding outlines is by photolithographic patterning and etch. Masking blocks 25-33 might be of the same or different composition from that of first material 20, with different
10 compositions being more preferred. Where for example such are formed of the same composition, one exemplary manner of forming masking blocks 28 relative to underlying material 20 is by a timed etch of the first material through openings formed in a mask, for example through openings formed in a photomask. Further by way of example only, an etch stop layer might be
15 received intermediate masking blocks 25-33 and underlying first material. For example and by way of example only, with respect to the Fig. 2 embodiment, layer 22 might be provided to constitute an etch stop layer provided intermediate masking blocks 25-33 and underlying first material 24 (not shown). The exemplary depicted array pattern of masking blocks 25-33
20 is exemplary only, with essentially any other existing or yet-to-be developed array pattern also being contemplated. In a depicted exemplary embodiment, and by way of example only, an exemplary spacing between immediately adjacent masking blocks in a row (i.e. between the right edge of masking block 28 and the left edge of masking block 29) is 500 Angstroms.
25 An exemplary spacing between immediately adjacent masking blocks in a column (i.e. between the lower edge of masking block 26 and the upper edge of masking block 29 in Fig. 3) is 500 Angstroms. An exemplary analogous diagonal spacing between diagonally adjacent masking blocks (i.e. between blocks 31 and 29) is 750 Angstroms.

Referring to Figs. 6 and 7, a layer of second material 36 has been
30 deposited over masking blocks 25-33 and over first material 20 received between masking blocks 25-33. In one aspect, second material 36 is of different composition from that of masking blocks 25-33. By way of example only where material 20 is BPSG and masking blocks 25-33 are BPSG or
35 undoped silicon dioxide, exemplary preferred materials for layer 36 include

silicon nitride, aluminum oxide, and hafnium oxide. Of course, other insulative, and even conductive and semiconductive, materials might be utilized for material 36. An exemplary semiconductive material comprises polysilicon. Exemplary electrically conductive materials include titanium
5 nitride, tantalum nitride, and tungsten. An exemplary deposition thickness for layer 36 is from 250 Angstroms to 300 Angstroms.

Referring to Figs. 8-10, layer of second material 36 has been anisotropically etched effective to expose masking blocks 25-33 and form an interconnected retaining structure 40 against sidewalls of the depicted
10 masking blocks 25-33. Further, interconnected retaining structure 40 exposes some of first material 20 received between the depicted masking blocks in the depicted exemplary embodiment. By way of example only, such exposed first material 20 is between diagonally adjacent masking blocks, although other position openings are of course contemplated and
15 likely dependent upon the array patterning of the masking blocks. Further in the depicted preferred embodiment, retaining structure 40 directly contacts sidewalls of the depicted masking blocks. In the depicted and most preferred embodiment, retaining structure 40 is formed at least in part by etching layer of material 36 whereby such is not masked anywhere within
20 capacitor array area 14 to form such retaining structure 40. Further in one exemplary preferred embodiment, structure 40 might be so formed without any of layer of material 36 being masked anywhere on the substrate to form such retaining structure. For example and by way of example only, Figs. 9 and 10 depict no masking occurring within peripheral circuitry area 16 such
25 that all material 36 is removed therefrom. Alternately of course, layer of material 36 as/when extending to be received over peripheral area 16 might be at least partially masked in such peripheral area during the anisotropic etching (not shown) such that at least some of it remains after such etching.

Referring to Figs. 11-13, exposed first material 20 received between
30 masking blocks 25-33 has been masked with a third material 44. In one aspect, third material 44 is of different composition from that of first material 20, from that of masking blocks 25-33, and from that of second material 36. Where material 20 is BPSG, where masking blocks 25-33 comprise doped or undoped silicon dioxide, and where layer of material 36
35 comprises silicon nitride, an exemplary material 44 is polysilicon.

Regardless, one exemplary preferred technique for forming the Figs. 11-13 construction is by deposition of material 44 followed by chemical-mechanical polishing of it effective to expose masking blocks 25-33. Figs. 12 and 13 depict some remnant material 44 remaining within peripheral circuitry area 16, although of course material 44 might alternately be completely removed within peripheral area 16 at this point of the preferred processing. Further in one exemplary implementation, at least one of materials 25-33, material 36 and 44 comprises amorphous carbon, and in another implementation comprises polysilicon. Further of course in one aspect, at least one of material 25-33, material 36, and material 44 comprises amorphous carbon and at least another one of such materials comprises polysilicon.

Referring to Figs. 14 and 15, masking blocks 25-33 have been etched followed by etching (anisotropic) of first material 20 thereunder substantially selectively relative to second material 36 and third material 44 effective to form capacitor electrode openings 25c, 26c, 27c, 28c, 29c, 30c, 31c, 32c, and 33c. (Openings 25c, 26c, 27c, 30c, 32c and 33c are not shown in Figs. 14 and 15, but do appear and are so designated in subsequent figures.) In the context of this document, a substantially selective etch requires a removal rate of the removed material relative to the stated other material(s) at a removal ratio of at least 15:1. In the depicted example where third material 44 remains masking material 20 within peripheral circuitry area 16, material 20 remains within such peripheral area. If no masking material 44 were received over material 20 in such area, all such material 20 in the peripheral circuitry area would likely be removed at this point of processing.

Referring to Figs. 16-18, individual capacitor electrodes 25d, 26d, 27d, 28d, 29d, 30d, 31d, 32d, and 33d have been formed within individual of the respective capacitor electrode openings and against interconnected retaining structure 40. By way of example only, an exemplary preferred manner of forming the same is by deposition of a titanium nitride layer to a suitable thickness, followed by chemical-mechanical polishing thereof. In the depicted preferred and exemplary embodiments, the layer from which the capacitor electrodes are formed is deposited to less than completely fill the respective capacitor electrode openings such that the resultant

individual of the capacitor electrodes comprises a container shape. Of course, other electrode shapes are contemplated, including by way of example only completely plugging of the capacitor electrode openings with conductive material for formation of capacitor electrodes.

5 Referring to Figs. 19 and 20, third material 44 (not shown) has been etched substantially selectively relative to second material 36 and substantially selectively relative to the capacitor electrodes 25d-33d effective to expose first material 20 beneath the etched third material.

10 Referring to Figs. 21 and 22, after such etching of the third material 44, at least some of the exposed first material 20 has been etched substantially selectively relative to capacitor electrodes 25d-33d and substantially selectively relative to second material 36 effective to expose outer lateral sidewalls of capacitor electrodes 25d-33d, and to leave at least some of second material 36 of the interconnected retaining structure 40 at
15 least in part supporting capacitor electrodes 25d-33d. In the depicted and preferred embodiment, such etching has been of substantially all of first material 20 such that substantially all of the outer lateral sidewalls of the capacitor electrodes have been exposed.

One implementation of the invention contemplates at least some
20 etching of material 36 of retaining structure 40 prior to deposition of third material 44. Such is shown by way of example only with respect to Fig. 25 in connection with an alternate embodiment substrate fragment 10g. Like numerals from the first described embodiments have been utilized as appropriate, with differences being indicated with the suffix "g". Fig. 25 depicts some etching having occurred relative to the retaining structure such that a retaining structure 40g results by a degree of etching which is effective to open up the spaces of exposed material 20. For example, the depicted dash lines show the initial openings as depicted in the first embodiment, with the solid line outlines thereabout depicting such widening
25 resulting from a suitable exemplary facet etch or a suitable exemplary wet etch of material 26. By way of example only where, for example, material 36g comprises silicon nitride, an exemplary wet etching chemistry for producing the Fig. 25 structure same includes phosphoric acid. An exemplary facet etch technique would include argon plasma at from 100W
30 to 1000W RF power, and from 25°C to 100°C.

Referring to Figs. 23 and 24, capacitor dielectric material 50 and capacitor electrode material 60 have been deposited at least below retaining structure 40 over at least some of the outer lateral sidewalls of the capacitor electrodes as-shown. Any suitable existing or yet-to-be developed materials are of course contemplated. In the depicted exemplary embodiment, capacitor electrode material 60 is shown as constituting a common capacitor electrode among a plurality of capacitors. Of course alternately by way of example only, such might be patterned or otherwise formed to constitute a separate capacitor electrode for each capacitor or for a group of capacitors. In the depicted preferred embodiment, retaining structure 40 remains as part of a finished integrated circuitry construction incorporating a plurality of capacitors.

In one aspect, an implementation of the invention can be considered as a method of forming a plurality of capacitors which includes forming different composition first, second, and third materials over a capacitor electrode-forming material. By way of example only, material of masking blocks 25-33 constitutes an exemplary first material, material 36 constitutes an exemplary second material, and material 44 constitutes an exemplary third material, with all of such being received over an exemplary capacitor electrode-forming material 20. First, second and third materials are received at least in part at some common elevation over the capacitor electrode-forming material. By way of example only, Fig. 12 depicts an exemplary such elevation "H". The second material comprises an anisotropically etched retaining structure.

Such first material is etched substantially selectively relative to the second and third materials followed by etching of the capacitor electrode-forming material substantially selectively relative to the second and third materials effective to form a plurality of capacitor electrode openings. By way of example only, the above described processing relative to the figures is but one exemplary technique. Individual capacitor electrodes are formed within individual of the capacitor electrode openings.

Thereafter, the third material is etched substantially selectively relative to the second material and substantially selectively relative to the capacitor electrodes effective to expose capacitor electrode-forming material underlying the third material which was/is being etched. This is followed by

etching the capacitor electrode-forming material substantially selectively relative to the second material and substantially selectively relative to the capacitor electrodes effective to expose outer lateral sidewalls of the capacitor electrodes. Only some or all of the capacitor electrode-forming material might be etched. Regardless, such etching is also effective to leave at least some of the retaining structure at least in part supporting the plurality of capacitor electrodes. The plurality of capacitor electrodes is incorporated into a plurality of capacitors.

One implementation of an aspect of the invention includes a method of forming a plurality of capacitors whereby a plurality of capacitor electrodes is provided within a capacitor array area over a substrate, and whereby the capacitor electrodes comprise outer lateral sidewalls. Such a method includes supporting the plurality of capacitor electrodes at least in part with a retaining structure which engages the outer lateral sidewalls. The retaining structure is formed at least in part by etching a layer of material which is not masked anywhere within the capacitor array area to form such retaining structure. The above described preferred processing of providing a plurality of capacitor electrodes and supporting the same with a retaining structure as described above is but only one exemplary embodiment of this implementation as just so stated. The plurality of capacitor electrodes is incorporated into a plurality of capacitors, for example and by way of example only as described above. In the above described exemplary embodiments, such etching to form the retaining structure occurs prior to formation of the plurality of capacitor electrodes. However, an aspect of the invention contemplates etching to form the retaining structure after formation of the plurality of capacitor electrodes.

In compliance with the statute, the invention has been described in language more or less specific as to structural and methodical features. It is to be understood, however, that the invention is not limited to the specific features shown and described, since the means herein disclosed comprise preferred forms of putting the invention into effect. The invention is, therefore, claimed in any of its forms or modifications within the proper scope of the appended claims appropriately interpreted in accordance with the doctrine of equivalents.

CLAIMS

What is claimed is:

5 1. A method of forming a plurality of capacitors, comprising:
 providing a plurality of capacitor electrodes within a capacitor array
 area over a substrate, the capacitor electrodes comprising outer lateral
 sidewalls;

 supporting the plurality of capacitor electrodes at least in part with a
10 retaining structure which engages the outer lateral sidewalls, the retaining
 structure being formed at least in part by etching a layer of material which is
 not masked anywhere within the capacitor array area to form said retaining
 structure; and

 incorporating the plurality of capacitor electrodes into a plurality of
15 capacitors.

 2. The method of claim 1 wherein said etching occurs prior to
 formation of the plurality of capacitor electrodes.

20 3. The method of claim 1 wherein said etching occurs after
 formation of the plurality of capacitor electrodes.

 4. The method of claim 1 comprising a circuitry area peripheral to
 the capacitor array area, said layer of material extending to over the
25 peripheral area during said etching and being at least partially masked in
 said peripheral area during said etching.

 5. The method of claim 1 wherein said layer of material is not
 masked anywhere on the substrate during said etching.

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 6. The method of claim 1 wherein individual of the capacitor
 electrodes comprises a container shape.

7. The method of claim 1 wherein the retaining structure remains as part of a finished integrated circuitry construction incorporating the plurality of capacitors.

5 8. The method of claim 1 wherein said material is electrically insulative.

9. The method of claim 1 wherein said material is electrically conductive.

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10. The method of claim 1 wherein said material is semiconductive.

11. A method of forming a plurality of capacitors, comprising:
providing a plurality of capacitor electrodes over a substrate, the
15 capacitor electrodes comprising outer lateral sidewalls;
supporting the plurality of capacitor electrodes at least in part with a retaining structure which engages the outer lateral sidewalls, the retaining structure being formed at least in part by etching a layer of material which is not masked anywhere on the substrate to form said retaining structure; and
20 incorporating the plurality of capacitor electrodes into a plurality of capacitors.

12. The method of claim 11 wherein individual of the capacitor electrodes comprises a container shape.

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13. The method of claim 11 wherein the retaining structure remains as part of a finished integrated circuitry construction incorporating the plurality of capacitors.

30 14. The method of claim 11 wherein said material is electrically insulative.

15. The method of claim 11 wherein said material is electrically conductive.

16. The method of claim 11 wherein said material is semiconductive.

17. The method of claim 11 wherein said etching occurs prior to
5 formation of the plurality of capacitor electrodes.

18. The method of claim 11 wherein said etching occurs after formation of the plurality of capacitor electrodes.

10 19. A method of forming a plurality of capacitors, comprising:
forming different composition first, second and third materials over a capacitor electrode-forming material; said first, second and third materials being received at least in part at some common elevation over the capacitor electrode-forming material; the second material comprising an
15 anisotropically etched retaining structure;
etching the first material substantially selectively relative to the second and third materials followed by etching the capacitor electrode-forming material substantially selectively relative to the second and third materials effective to form a plurality of capacitor electrode openings;
20 forming individual capacitor electrodes within individual of the capacitor electrode openings;
etching the third material substantially selectively relative to the second material and substantially selectively relative to the capacitor electrodes effective to expose capacitor electrode-forming material
25 underlying said third material being etched, followed by etching said capacitor electrode-forming material substantially selectively relative to the second material and substantially selectively relative to the capacitor electrodes effective to expose outer lateral sidewalls of the capacitor electrodes and leave at least some of the retaining structure supporting the
30 capacitor electrodes; and
incorporating the plurality of capacitor electrodes into a plurality of capacitors.

20. The method of claim 19 wherein the first material is different in
35 composition from that of the capacitor electrode-forming material.

21. The method of claim 19 wherein the first material is of the same composition as that of the capacitor electrode-forming material.

22. The method of claim 19 wherein the capacitor electrode-forming material comprises at least two layers, one of the two layers comprising an etch stop layer received proximate the first, second, and third materials.

23. The method of claim 19 wherein the first material is formed prior the second material and the second material is formed prior to the third material, and further comprising facet etching the retaining structure prior to forming the third material.

24. The method of claim 19 wherein the first material is formed prior the second material and the second material is formed prior to the third material, and further comprising wet etching the retaining structure prior to forming the third material.

25. The method of claim 19 wherein individual of the capacitor electrodes comprises a container shape.

26. The method of claim 19 wherein the capacitor electrode openings are formed within a capacitor array area over the substrate, the substrate comprising circuitry area peripheral to the capacitor array area, the anisotropic etching of the second material to form the retaining structure being conducted without any masking of said second material within the capacitor array area to form said retaining structure.

27. The method of claim 26 wherein the anisotropic etching of the second material to form the retaining structure is conducted without any masking of said second material anywhere on the substrate to form said retaining structure.

28. The method of claim 19 wherein the retaining structure remains as part of a finished integrated circuitry construction incorporating the plurality of capacitors.

29. The method of claim 19 wherein the second material is electrically insulative.

30. The method of claim 19 wherein the second material is
5 electrically conductive.

31. The method of claim 19 wherein the second material is semiconductive.

10 32. A method of forming a plurality of capacitors, comprising:
forming a plurality of spaced masking blocks over a first material, the masking blocks defining respective capacitor electrode opening outlines thereunder;

15 depositing a layer of second material over the masking blocks and over first material received between the masking blocks, the second material being of different composition from that of the masking blocks;

anisotropically etching the layer of second material effective to expose the masking blocks and form an interconnected retaining structure against sidewalls of the masking blocks, the interconnected retaining
20 structure exposing some of the first material received between the masking blocks;

after the anisotropic etching, masking the exposed first material received between the masking blocks with a third material; the third material being of different composition from that of the first material, from that of the
25 masking blocks and from that of the second material;

etching the masking blocks and then the first material thereunder substantially selectively relative to the second and third materials effective to form capacitor electrode openings within the first material;

30 forming individual capacitor electrodes within individual of the capacitor electrode openings and against the interconnected retaining structure;

35 etching the third material substantially selectively relative to the second material and substantially selectively relative to the capacitor electrodes effective to expose first material beneath the etched third material;

after said etching of the third material, etching at least some of the exposed first material substantially selectively relative to the capacitor electrodes and substantially selectively relative to the second material effective to expose outer lateral sidewalls of the capacitor electrodes and
5 leave at least some of the second material of the interconnected retaining structure at least in part supporting the capacitor electrodes; and

after said etching of the first material effective to expose outer lateral sidewalls of the capacitor electrodes, depositing capacitor dielectric material and capacitor electrode material below the retaining structure over at least
10 some of said outer lateral sidewalls.

33. The method of claim 32 wherein the masking blocks are of a different composition from that of the first material.

15 34. The method of claim 32 wherein the masking blocks are of the same composition as that of the first material.

35. The method of claim 34 wherein the masking blocks are formed by a timed etch of the first material through mask openings.

20 36. The method of claim 35 wherein the timed etch is conducted through openings formed in a photomask.

37. The method of claim 32 comprising an etch stop layer received
25 intermediate the masking blocks and the first material.

38. The method of claim 32 wherein the capacitor electrode openings are formed within a capacitor array area over the substrate, the substrate comprising circuitry area peripheral to the capacitor array area,
30 the anisotropic etching of the layer of second material to form the retaining structure being conducted without any masking of said layer of second material within the capacitor array area to form said retaining structure.

39. The method of claim 38 wherein the anisotropic etching of the layer of second material to form the retaining structure is conducted without any masking of said layer of second material anywhere on the substrate to form said retaining structure.

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40. The method of claim 32 wherein individual of the capacitor electrodes comprises a container shape.

41. The method of claim 32 wherein the retaining structure remains as part of a finished integrated circuitry construction incorporating the plurality of capacitors.

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42. The method of claim 32 wherein at least one of the first, second and third materials comprises amorphous carbon.

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43. The method of claim 32 wherein at least one of the first, second and third materials comprises polysilicon.

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44. The method of claim 32 wherein at least one of the first, second and third materials comprises amorphous carbon and at least another one of the first, second and third materials comprises polysilicon.

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45. The method of claim 32 further comprising facet etching the retaining structure prior to forming the third material.

46. The method of claim 32 further comprising wet etching the retaining structure prior to forming the third material.

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